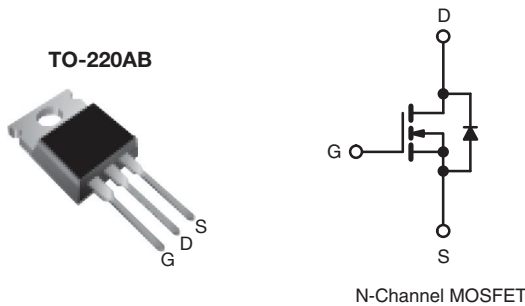


## Power MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V)	1000
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$ 11
$Q_g$ (Max.) (nC)	38
$Q_{gs}$ (nC)	4.9
$Q_{gd}$ (nC)	22
Configuration	Single



### FEATURES

- Dynamic  $dV/dt$  Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRFBG20PbF SiHFBG20-E3
SnPb	IRFBG20 SiHFBG20

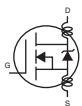
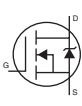
ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	1000	V	
Gate-Source Voltage		$V_{GS}$	$\pm 20$		
Continuous Drain Current	$V_{GS}$ at 10 V	$I_D$	$T_C = 25\text{ }^\circ\text{C}$	1.4	A
			$T_C = 100\text{ }^\circ\text{C}$	0.86	
Pulsed Drain Current <sup>a</sup>		$I_{DM}$	5.6		
Linear Derating Factor			0.43	W/ $^\circ\text{C}$	
Single Pulse Avalanche Energy <sup>b</sup>		$E_{AS}$	200	mJ	
Repetitive Avalanche Current <sup>a</sup>		$I_{AR}$	1.4	A	
Repetitive Avalanche Energy <sup>a</sup>		$E_{AR}$	5.4	mJ	
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	54	W	
Peak Diode Recovery $dV/dt^c$		$dV/dt$	1.0	V/ns	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to + 150	$^\circ\text{C}$	
Soldering Recommendations (Peak Temperature)	for 10 s		300 <sup>d</sup>		
Mounting Torque	6-32 or M3 screw		10		lbf · in
			1.1	N · m	

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 193\text{ }\mu\text{H}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 1.4\text{ A}$  (see fig. 12).
- $I_{SD} \leq 1.4\text{ A}$ ,  $dI/dt \leq 60\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 600$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	2.3	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		1000	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	1.2	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 1000\text{ V}, V_{GS} = 0\text{ V}$		-	-	100	$\mu\text{A}$
		$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 0.84\text{ A}^b$	-	-	11	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 0.84\text{ A}^b$		1.0	-	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5		-	500	-	pF
Output Capacitance	$C_{oss}$			-	52	-	
Reverse Transfer Capacitance	$C_{rss}$			-	17	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 1.4\text{ A}, V_{DS} = 400\text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	-	38	nC
Gate-Source Charge	$Q_{gs}$			-	-	4.9	
Gate-Drain Charge	$Q_{gd}$			-	-	22	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 500\text{ V}, I_D = 1.4\text{ A}, R_g = 18\text{ }\Omega, R_D = 370\text{ }\Omega$ , see fig. 10 <sup>b</sup>		-	9.4	-	ns
Rise Time	$t_r$			-	17	-	
Turn-Off Delay Time	$t_{d(off)}$			-	58	-	
Fall Time	$t_f$			-	31	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	$L_S$			-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	1.4	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	-	5.6	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 1.4\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 1.4\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	130	190	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	0.46	0.69	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

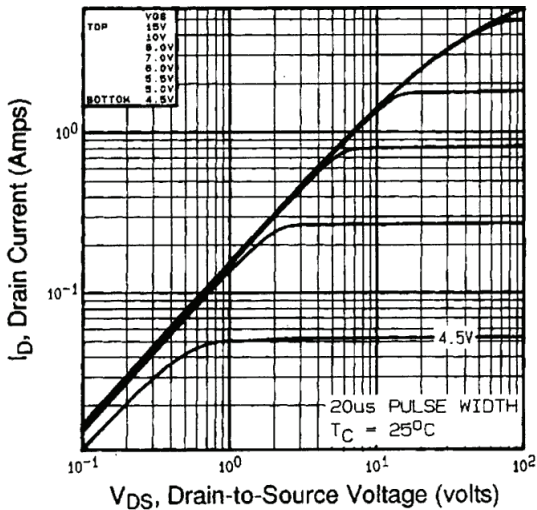


Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$

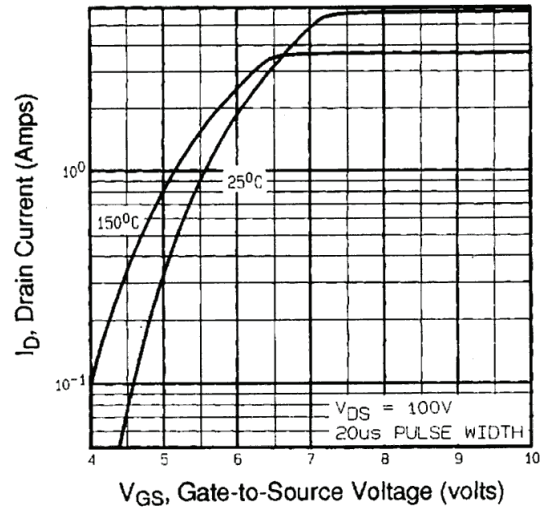


Fig. 3 - Typical Transfer Characteristics

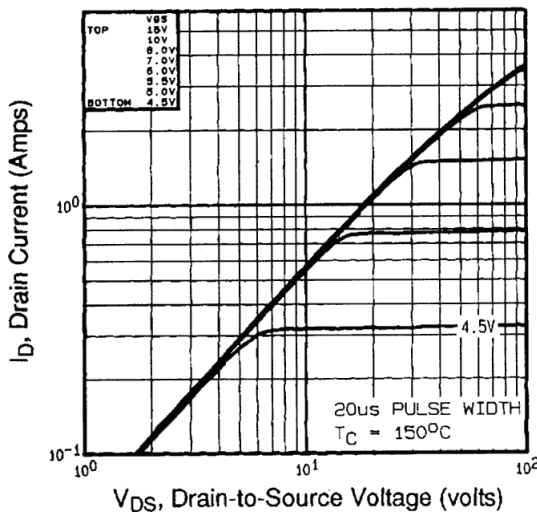


Fig. 2 - Typical Output Characteristics,  $T_C = 150^\circ\text{C}$

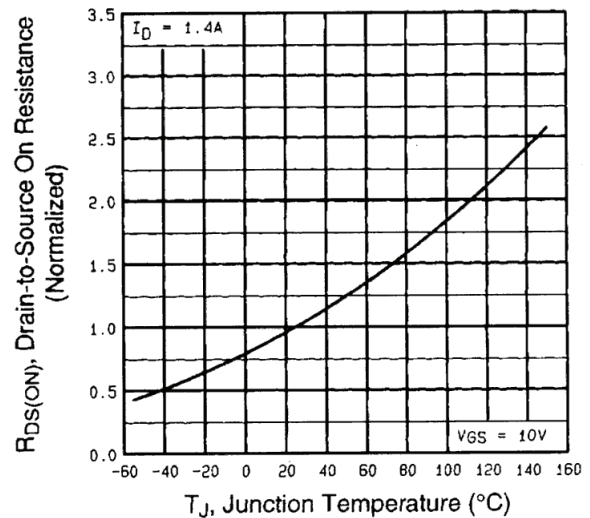


Fig. 4 - Normalized On-Resistance vs. Temperature

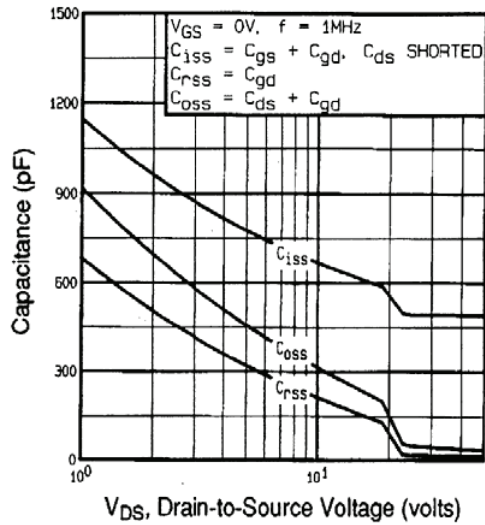


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

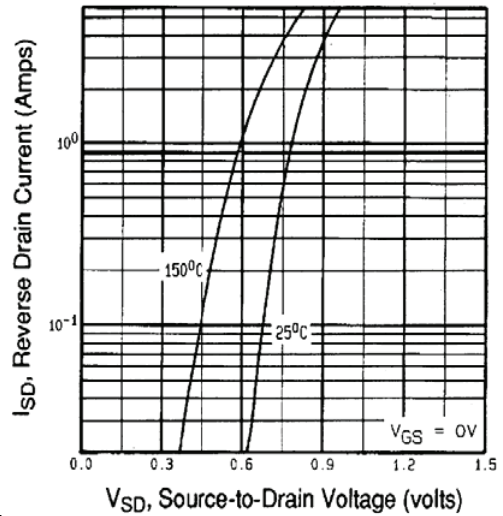


Fig. 7 - Typical Source-Drain Diode Forward Voltage

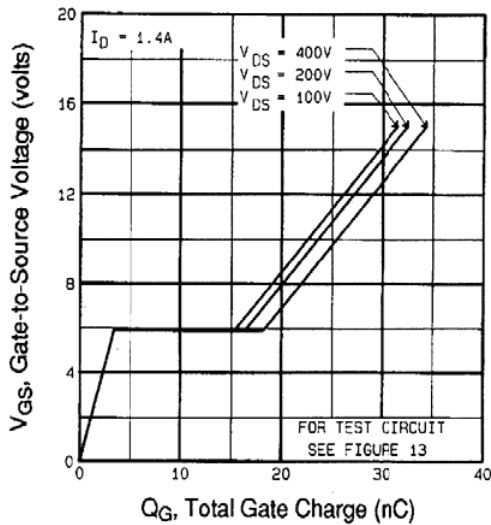


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

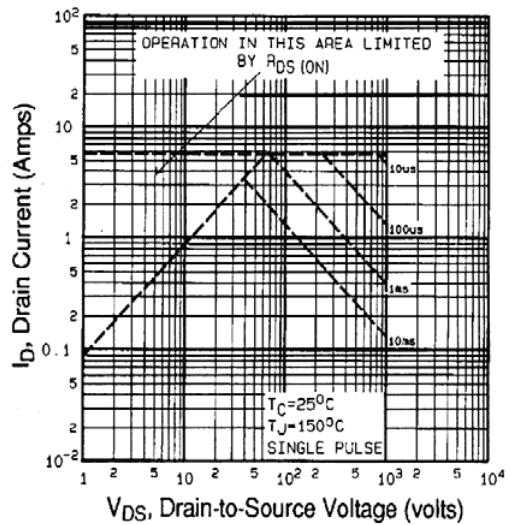


Fig. 8 - Maximum Safe Operating Area

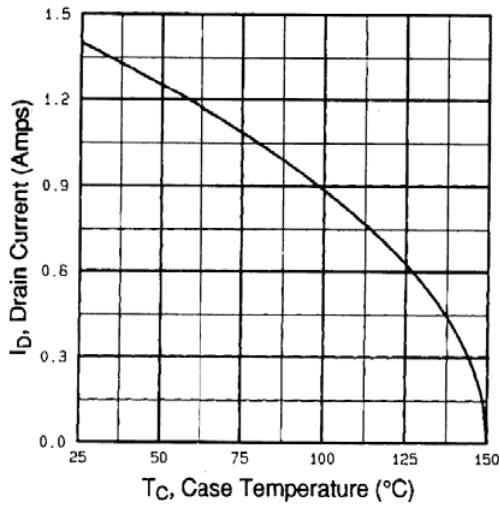


Fig. 9 - Maximum Drain Current vs. Case Temperature

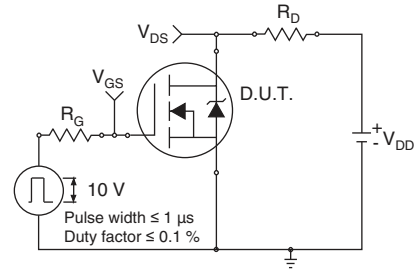


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

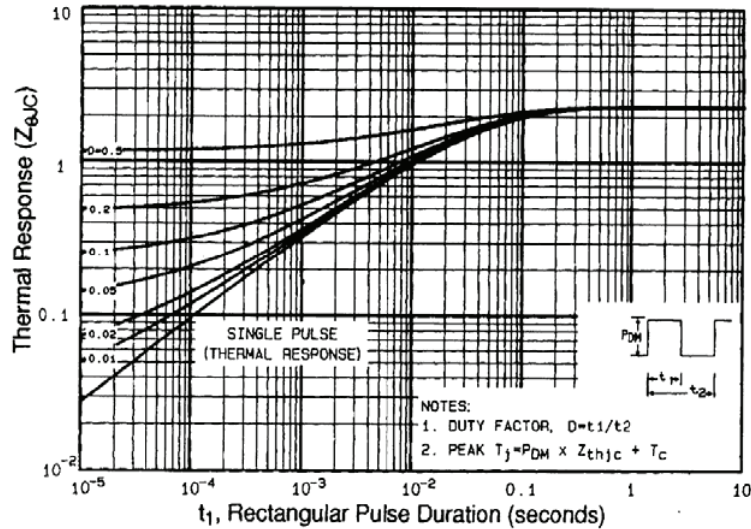


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

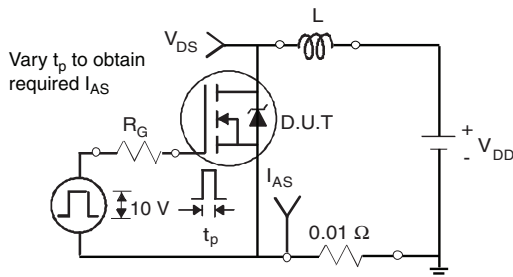


Fig. 12a - Unclamped Inductive Test Circuit

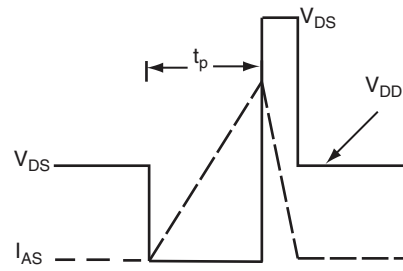


Fig. 12b - Unclamped Inductive Waveforms

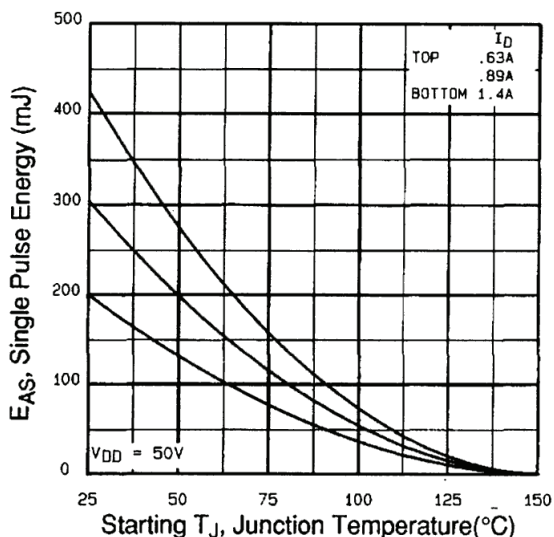


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

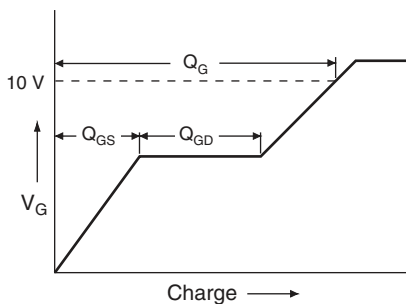


Fig. 13a - Basic Gate Charge Waveform

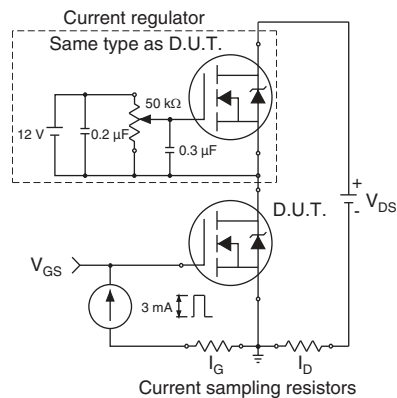
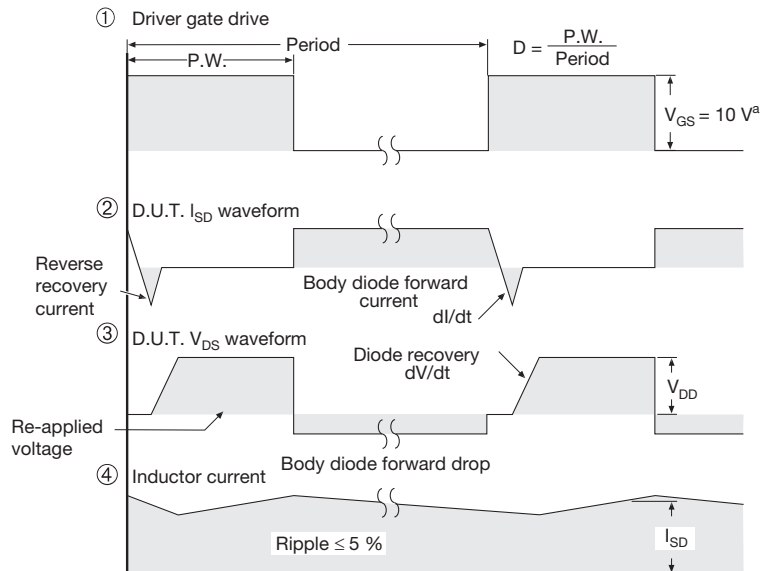
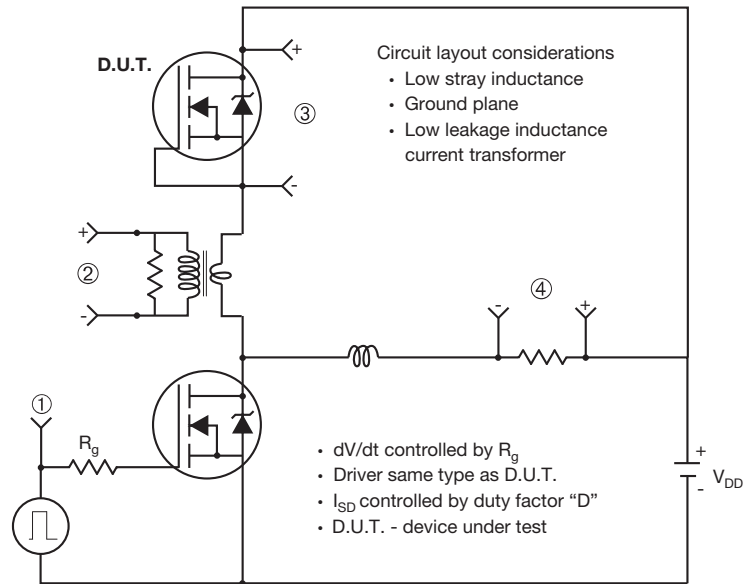


Fig. 13b - Gate Charge Test Circuit

### Peak Diode Recovery dV/dt Test Circuit



**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?91123](http://www.vishay.com/ppg?91123).

## TO-220AB

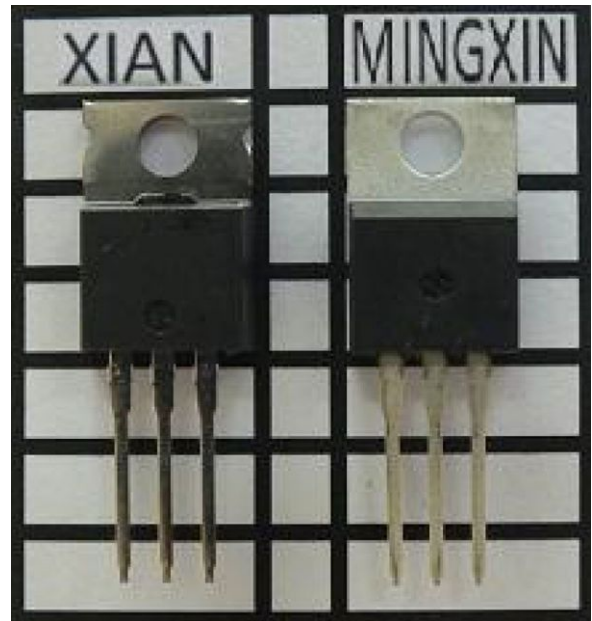


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12  
DWG: 5471

**Notes**

- \* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM
- Xi'an and Mingxin actual photo





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<http://moschip.ru/get-element>

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### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

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